



Product data sheet

1. General description

Dual ultrafast power diodes in a TO220 plastic package.

2. Features and benefits

- Low forward voltage drop
- Low leakage current
- Soft reverse recovery characteristics
- High thermal cycling performance

3. Applications

- Home appliance power supply
- Discontinuous Current Mode (DCM) Power Factor Correction (PFC)

4. Quick reference data

able 1. Q	uick reference data					
Symbol	Parameter	Conditions	Values		Unit	
Absolute	maximum rating					
V _R	repetitive peak reverse voltage	DC	600		V	
I _{O(AV)}	average forward current	δ = 0.5; T _{mb} ≤ 124 °C; square-wave pulse; both diodes conducting	20		A	
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _{mb} ≤ 140 °C; square-wave pulse; per diode	20		A	
I _{FSM} non-repetitive peak forward current		t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4	120			A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode	132			A
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics	·				
V _F	forward voltage	I_{F} = 10 A; T_{j} = 25 °C; per diode; <u>Fig. 6</u>	-	1.3	1.7	V
		$I_F = 10 \text{ A}; T_j = 150 \text{ °C}; \text{ per diode}; Fig. 6$	-	1.0	1.35	V
Dynamic	characteristics	·				
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ per diode}; Fig. 7$	-	30	50	ns
		$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ per diode}; Fig. 7$	-	40	55	ns
		$I_F = 0.5 \text{ A}; I_r = 0.25 \text{ A}; I_R = 1 \text{ A};$ $T_i = 25 \text{ °C}; \text{ per diode}$	-	-	35	ns

Table 1. Quick reference data

5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1		
2	К	cathode		
3	A2	anode 2		K
mb	К	mounting base; connected to cathode		sym125

6. Ordering information

Table 3. Ordering information								
Type number	Package	Orderable part number	Packing	Small packing	Package	Package		
	Name		method	quantity	version	issue date		
BYV410-600P	TO220	BYV410-600PQ	Tube	50	TO220E	26-April-2019		

7. Marking

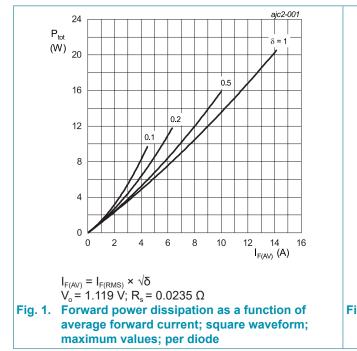
Table 4. Marking codes							
Type number	Marking codes						
BYV410-600P	BYV410-600P						

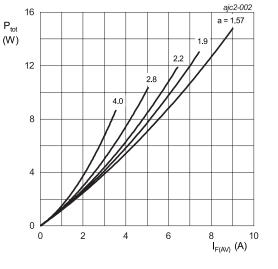
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		600	V
V_{RWM}	crest working reverse voltage		600	V
V _R	reverse voltage	DC	600	V
I _{O(AV)}	average forward current	δ = 0.5; T _{mb} ≤ 124 °C; square-wave pulse; both diodes conducting; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	20	A
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _{mb} ≤ 140 °C; square-wave pulse; per diode	20	A
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4	120	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode	132	A
T _{stg}	storage temperature		-55 to 175	°C
T _j	junction temperature		175	°C

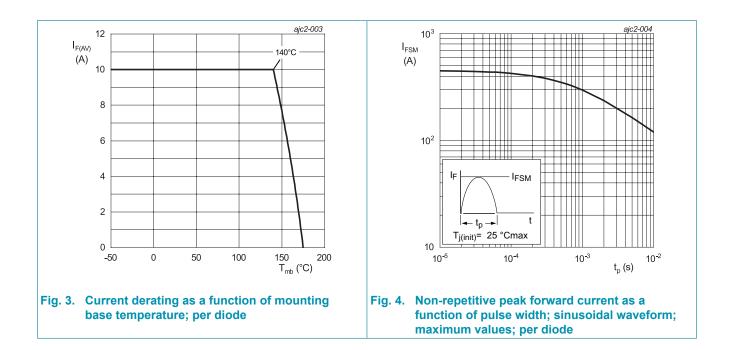




 a = form factor = I_{F(RMS)} / I_{F(AV)} V_o = 1.119 V; R_s = 0.0235 Ω
Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values; per diode

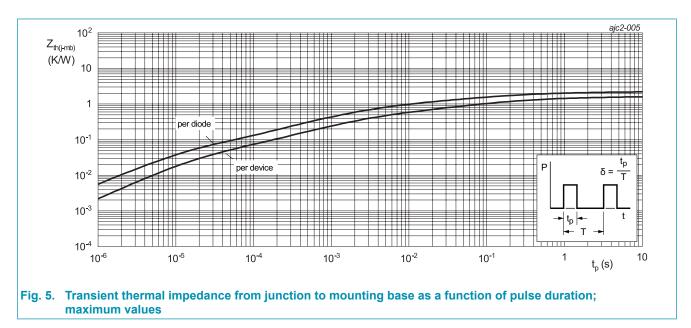
Dual ultrafast power diode

BYV410-600P



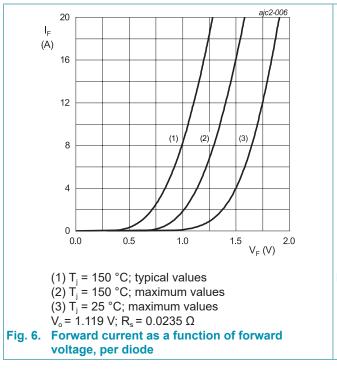
9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to	with heatsink compound; per diode; Fig. 5	-	-	2.2	K/W
	mounting base	with heatsink compound; both diodes conducting; Fig. 5	-	-	1.6	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air	-	55	-	K/W



10. Characteristics

Table 7. Cl	haracteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _F	forward voltage	I _F = 10 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.3	1.7	V
		I _F = 10 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.0	1.35	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	1	10	μA
		V _R = 600 V; T _j = 150 °C	-	0.1	0.5	mA
Dynamic	characteristics					
Q _r	recovered charge	I _F = 1 A; V _R = 30 V; dI _F /dt = 100 A/μs; T _j = 25 °C; per diode; <u>Fig. 7</u>	-	22	-	nC
t _{rr}	reverse recovery time	I _F = 1 A; V _R = 30 V; dI _F /dt = 100 A/μs; T _j = 25 °C; per diode; <u>Fig. 7</u>	-	30	50	ns
		$I_F = 1 \text{ A}; V_R = 30 \text{ V}; \text{ d}I_F/\text{d}t = 50 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ per diode}; Fig. 7$	-	40	55	ns
		$I_F = 0.5 \text{ A}; I_r = 0.25 \text{ A}; I_R = 1 \text{ A};$ $T_j = 25 \text{ °C}; \text{ per diode}$	-	-	35	ns
I _{RM}	peak reverse recovery current	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ per diode}; Fig. 7$	-	1.6	-	A
		$I_F = 1 \text{ A}; V_R = 30 \text{ V}; \text{ d}I_F/\text{d}t = 50 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ per diode}; Fig. 7$	-	1.1	-	A
E _{as}	non-repetitive avalanche energy	I _R = 4.8 A; T _{j(init)} = 25 °C; L = 15 mH	130	175	-	mJ



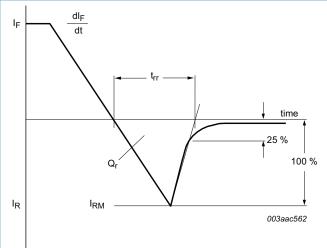
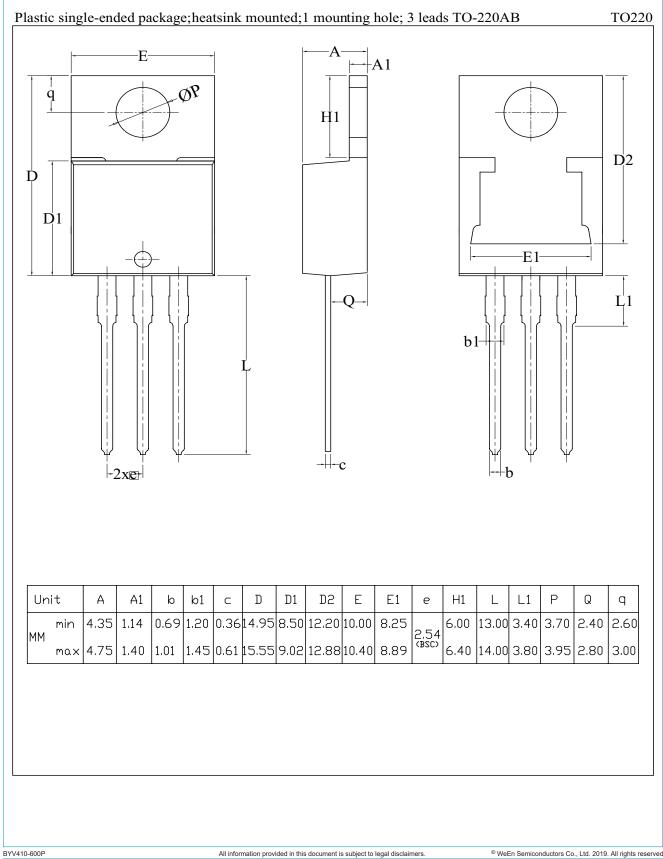


Fig. 7. Reverse recovery definitions; ramp recovery

11. Package outline



BYV410-600P

Dual ultrafast power diode

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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